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**Patentanmeldung Nr.    Patent application No.    Demande de brevet n°**

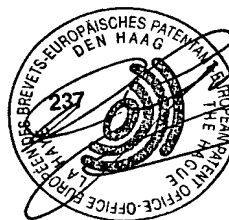
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Bezeichnung der Erfindung/Title of the invention/Titre de l'invention:  
(Falls die Bezeichnung der Erfindung nicht angegeben ist, siehe Beschreibung.  
If no title is shown please refer to the description.  
Si aucun titre n'est indiqué se referer à la description.)

Phase-shift mask

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## Description

## Phase-Shift Mask

- 5 The present invention relates to a phase-shift mask having at least one first pattern, which is arranged in a two-dimensional matrix with a multiple of second patterns, which are substantially identical to said first pattern.
- 10 The minimum resolvable structure width of an exposure tool projection system for transferring a pattern structured on a mask onto a semiconductor wafer being coated with a resist given by the term  $0,25 \cdot \lambda / \text{NA}$  can theoretically be reached by
- 15 employing a full set of so-called litho-enhancement techniques. In the formula,  $\lambda$  is the wavelength of the illuminating light and NA is the numerical aperture of the pupil plane, or the object lens system, respectively. The coefficient  $k_1 = 0,25$  is extraordinarily challenging, and said techniques are either not yet appropriately matured or operate
- 20 only under restricted conditions, e.g., for certain patterns on the mask.

Typical exposure tools operate with  $k_1 = 0,4$  for simple periodic lines-and-spaces patterns. A most promising candidate

25 for imaging down the minimum structure width to  $0,3 \cdot \lambda / \text{NA}$  derives from the use of alternating phase-shift masks. While not yet in a production status this kind of masks advantageously enhances the resolution capability of a projection system in combination with said lines-and-spaces patterns.

30 E.g., chrome lines are alternately separated by spaces having two opposite degrees of phase-shift, which is exerted on the light, that traverses the mask to expose the wafer. The alternating degree of phase-shift considerably enhances the amount of structure contrast.

35

While it is a straightforward approach to apply alternating phase-shifts to transparent portions of the patterns, i.e.

spaces, in a one-dimensional grid of structures, i.e. lines and spaces, an application in two-dimensional periodic structures is more complicated. For example, a dense structure matrix of contact holes necessitates, that in the case of alternating phase-shift masks there are always two neighbouring contact holes, which in being transparent both comprise the feature of the same phase-shift. The assignment of two phases allows either to get maximum contrast in y-direction or a maximum contrast in x-direction, but no simultaneous improvement of the contrast is possible.

The use of attenuated phase-shift masks, or half-tone masks, is already matured, and is used in manufacturing of mask mass products. Unfortunately, attenuated phase-shift masks do not have the resolution capability for exposure tools as in the case of alternating phase-shift masks, or their chromeless supplements. The practice of manufacturing all kinds of phase-shift masks stated above is well-known to ordinary persons skilled in the art, and will not be described further herein.

It is therefore a primary objective of the present invention to overcome the above problems and to facilitate a higher resolution capability by improving the structure of phase-shift masks used to project a pattern onto a semiconductor wafer.

The objective is solved by a phase-shift mask having at least one first pattern, which is arranged in a two-dimensional matrix with a multiple of second patterns, which are substantially identical to said first pattern, said first pattern comprising at least a first portion having a first area, a first transmission of light, to be irradiated through said mask, a first phase-shift exerted on light traversing said mask through said first portion, at least a second portion having a second area, a second transmission of light to be irradiated through said mask, a second phase-shift exerted on

light traversing said mask through said second portion, said second phase-shift being different from said first phase-shift, characterised in that the product of said first area of said first portion times said first transmission, is substantially equal to the product of said second area of said second portion times said second transmission.

Further aspects are evident from the dependent claims.

10 According to the present invention a feature commonly utilized in alternating phase-shift masks is extended to two dimensions separately, and - in an aspect - applied to the case of attenuated phase-shift masks. The prior art feature is that a duty cycle of 1, i.e. the width of the line is equal  
15 to the width of the space in a lines-and-spaces pattern on an alternating phase-shift mask, leads to a vanishing zero diffraction order in the Fourier spectrum. This again implicitly results in a frequency doubling effect with respect to the number of structurable patterns per length unit. An extension  
20 to two orthogonal directions of this advantageous effect has not been applied with different duty cycles for each direction, yet. With the present invention, it is found, that basic shapes with the requirements of claim 1, thereby enabling duty cycles of the pattern matrix being different from one in  
25 two orthogonal directions can afford this extension, and thus provide a frequency doubling of structures in two dimensions.

In this document, particularly in the claims, if not stated otherwise, transmission of light through a mask denotes the  
30 percentage, or factor respectively, of electrical field strength, that is not absorbed or reflected by the mask, thus being transmitted. The power of light amplitude is determined from the square of the electrical field strength of said light traversing the mask.

35

It has been found, that in dependence of the transmission - as measured in terms of power of light - of half-tone phase-

shift masks, which typically amounts to 5 % to 7 % in conventional half-tone phase-shift masks, the areas of the respective portions providing the attenuated or non-attenuated light enabling a contrast-enhancing interference can be adjusted at the stage of design of the masks in order to provide the frequency doubling effect also in this type of masks.

A prerequisite of the present invention is, that a matrix of nearly similar patterns provides a larger structure to be projected onto a wafer. This means, that not only a first pattern is practically similar to a second pattern adjacently neighbouring the first pattern, but also that these patterns provide a periodic pitch in each direction. This pitch can vary between the first and the second dimension/direction on the mask.

With the term pattern as used in this document an element of said matrix structure is denoted, that is substantially identically repeated in both dimensions on the mask, and which directly borders to the next matrix element being the next pattern. Therefore, a phase-shift mask provides at least two portions within this pattern, the first having a first amount of phase-shift, e.g. 0, and a second portion having a second amount of phase-shift, e.g.  $\pi$ .

Particularly in the aspect of the transmission factors of the respective portions being different from each other, i.e. the phase-shift mask being a half-tone or attenuated phase-shift mask, the invention is characterized by a transmission-weighted surface area equivalence of these portions.

In the aspect of alternating phase-shift masks having extra chrome portions or chromeless phase-shift masks, there is some negligible amount of attenuation due to each of said portions, e.g. interference effects inside the etched quartz holes. The side effect of attenuation due to the quartz or



glass material of the mask will be disregarded here. In this document attenuation is considered to be due to a deposited surface layer material only, e.g. molybdenum-silicon or other phase-shifting materials.

5

The advantageous frequency doubling effect is found to arise, when the light contributions of the first and second portion having different phase-shifts are equal. In the former case of alternating phase-shift or chromeless masks this require-  
10 ments leads to the same size of the zero- and  $\pi$ -phase shifting portions, i.e. area of these portions. The area is to be taken as the two-dimensional surface measure of the portions as projected into the surface plane of the mask.

15 In the latter case of half-tone or attenuated phase-shift masks, said area of the attenuated phase-shifting portion, e.g. the second portion, has - according to the present invention - to alleviate its attenuation by having a larger area, which is larger by a factor being reciprocal to the  
20 transmission of light as being provided in terms of electrical field strength.

For example, a 5 % transmission - as provided in terms of power of light - would necessitate an area of the second portion  
25 being roughly 4 - 5 (square root of factor 20) times larger than the first portion, which is considered to reveal zero attenuation. 5 % transmission in terms of power of light corresponds to its square root of 22,36 % transmission of the electrical field strength.

30

Since in the case of dense structuring both structures, i.e. portions, would require large pattern sizes, low transition half-tone phase-shift masks would be comparatively ineffective with the present invention. Therefore, the present invention becomes particularly advantageous in the case of  
35 high-transition phase-shift masks, e.g. with attenuations larger than 0,5.

In a further aspect the case of chrome structures constituting a third portion is considered. In this case these non-transparent regions do not impact the requirements according to the present invention. The relevant feature according to the present invention is the relative area of the first and second portion being fully transparent or attenuating. The procedure of varying the area of a portion within a pattern as defined in this document is also called biasing at the design stage of a mask.

Further advantages and features of the present invention will be better understood by reference to embodiments taken in conjunction with the accompanying drawings, wherein

- 15 figure 1 shows the generation of diffraction orders in the pupil plane of the projection system,
- 20 figure 2 displays the vanishing zero diffraction order in a alternating phase-shift mask projection of a lines-and-spaces pattern,
- 25 figure 3 shows the vanishing zero diffraction order in a projection of a pattern according to the present invention of an attenuated phase-shift mask,
- 30 figure 4 the dependence of first diffraction order amplitude as a function of attenuation (added by one) for attenuated phase-shift masks as compared with other kinds of phase-shift masks,
- 35 figure 5 shows a first embodiment of a phase-shift mask pattern according to the present invention (a) and its result when projected onto a wafer (b),
- figure 6 same as figure 5 but for another pattern according to the present invention,

figure 7 same pattern as in figure 6, but shown with a different rotation angle, illustrating the frequency doubling on a semiconductor wafer,

5

figure 8 shows another embodiment of a pattern according to the present invention, referring to chromeless phase-shift masks,

10 figure 9 shows another embodiment of a pattern, similar to figure 8, but for attenuated phase-shift masks.

A schematic of an exposure tool, e.g. a projection stepper, is shown in Fig. 1. A periodic reticle structure comprising a multiple of patterns 3, 3' is projected from a phase-shift mask 1 through a lens 7 onto a semiconductor wafer 2 by irradiating light 8 at a given wavelength through said mask 1. The semiconductor wafer 2 is exposed and structured with a resolution depending on the pattern size on mask 1, the lens 7 characteristics and the aperture size enabling different Fourier diffraction orders to contribute to the image on semiconductor wafer 2, among others.

25 All diffraction orders in the Fourier spectrum, that are positioned at the distance of and within the pupil aperture form 6, contribute to the final image on the wafer. For a simple lines-and-spaces pattern, which is close to the resolution limit of the projection system, the amplitude of the first harmonic is an important parameter, that controls, e.g. 30 the image or structure contrast.

The principle of an alternating phase-shift mask is depicted in Fig. 2. In the side view of a lines-and-spaces pattern that forms a pattern 3, a first portion 100 is etched into the quartz material of the mask 1, thereby providing a phase-shift of, e.g.,  $\pi$ . A second portion 101 of pattern 3 is transparent but has not been etched, thus providing substan-

tially no phase-shift (0). These two portions 100, 101 constituting the alternately phase-shifting spaces are separated by non-transparent chrome structures 11.

- 5 The middle section of Fig. 2 shows the electrical field 40 of the light as emerging from the pattern 3, while in the bottom section the amplitudes of the diffraction orders in the pupil aperture 6 are displayed.
- 10 In the projection a different optical path length of these portions alters the phase of the electrical field 40 with respect to conventional chrome-on-glass masks as shown in Fig. 2. This feature leads to a frequency doubling due to vanishing zero order diffraction 20 in the frequency space. The amplitude of the first diffraction orders 21 can be calculated
- 15 to  $2,83/2\pi$ .

- There is no frequency doubling for chrome-on-glass masks (COG-masks) or conventional attenuated phase-shift masks
- 20 (HTPSM). Therefore, the Fourier spectra contain a zero diffraction order and the amplitude of the first harmonic is generally calculated to  $2/2\pi$  for chrome-on-glass masks and, e.g., to  $2,49/2\pi$  for attenuated phase-shift masks with 6 % transmission. Obviously, alternating phase-shift masks (APSM)
- 25 provide a superior contrast as compared with COG-masks or HTPSM.

- An embodiment of the present invention concerning HTPSM is depicted in the side view of Fig. 3, upper section. First
- 30 portions 101 having no attenuation and phase-shift are embedded in second portions 102 comprising a top layer of molybdenum-silicon, which attenuates and phase-shifts light 8 irradiated onto the mask 1. The electrical field strength 40 of light emerging from mask 1 is shown in the middle section of
- 35 Fig. 3. If - according to the present invention - the surface area 201 of the first portion 101 equals the surface area 202 of the second portion 102 times the transmission factor for

electrical field strength 40, the zero order diffraction 20 vanishes resulting in frequency doubling.

For simplicity the surface areas in Fig. 3 are displayed as  
5 arrows in a first direction, the second direction stretching the actual surface area is to be considered as orthogonal to the document plane.

In the diagram of Fig. 4 the first order harmonic amplitudes  
10 of a HTPSM being structured with a simple lines-and-spaces pattern are given as a function of transmission, as compared with the corresponding values for APSM ( $2,83/2\pi$ ), chromeless PSM ( $4,00/2\pi$ ) and conventionally structured 6 % HTPSM ( $2,49/2\pi$ ). For a transmission of an electrical field strength  
15 40 of 47 %, i.e. already a high-transition PSM, the first order harmonic becomes better than 6 % HTPSM, and for 56 % even the amplitude of an APSM is exceeded.

The extension to two dimensions is shown in Fig. 5, where a  
20 simple embodiment of the present invention of a pattern 3 comprising two fully transparent contact holes 301 (the first portion 101) on the mask 1 embedded in a semitransparent surroundings (second portion 102), which are positioned in a diagonal manner with respect to each other, is shown (left  
25 side). The imaged structures 302 on the semiconductor wafer 2 are also displayed (right side), when scaled to the same dimensions as mask 1. Frequency doubling is evident. The surface area of the attenuated region, i.e. the second portion 102, is weighed with the transmission according to the pres-  
30 ent invention, which results in vanishing zero order diffraction amplitudes. In Fig. 5a, right hand side, positions of the contact holes on the mask 1 are plotted over the imaged structures 302 on the wafer 2.

35 In Fig. 5b a situation of Fig 5a with a deviation (left side) from the condition of same sizes of the first and second portion weighted with the electrical field transmission of the

attenuated portion is compared with a situation substantially fulfilling this condition (right side), which accords to the present invention. If the contact holes become only slightly larger or smaller than said equivalence condition, frequency doubling is efficiently removed and a similar pattern structure as apparent from the mask 1 is imaged onto the wafer, i.e. a diagonal structure of contact holes 301.

Another embodiment, a mask 1 comprising a matrix of patterns 3 each made of just one contact hole 301, is given in Fig. 6. The relative positions in this embodiment are therefore grid-structured as compared to the diagonal structure of Fig. 5. The contact hole size is chosen to 180 nm x 180 nm at the design stage to give a surface area of the first fully transparent portion 101 of 32.400 nm<sup>2</sup>. The surrounding semitransparent second portion 102 of this HTPSM comprises 127.600 nm<sup>2</sup>. The transmission, which fulfills the condition according to the present invention, therefore amounts to roughly 25,4 % counted as electrical field strength transmission. The ordinarily provided power of light transmission of the corresponding HTPSM is then about 6,4 %. As can easily be inferred from Fig. 4 even more advantageous embodiments of high transition HTPSM, e.g., transmission of electrical light larger than 45 %, offer a larger contrast through larger first order harmonics. An electrical field transmission of 25,4 % corresponds to an attenuation of 74,6 %, giving the value

$$(x-1) = 1,746$$

in Fig. 4 on the x-axis. The first order amplitude amounts to roughly  $3,2/2\pi \dots 3,3/2\pi$ , which is better than those values for conventional HTPSM or APSM. In the case of no attenuation, i.e.

$$(x-1) = 2$$

the curve in Fig. 4 approaches to the chromeless PSM case. Nevertheless, the diagram of Fig. 4 is strictly valid only for the case of lines-and-spaces patterns.

A situation of deviation from this embodiment is displayed in Fig. 6b, analogously to Fig. 5b.

In Fig. 7, a similar embodiment as that shown in Fig. 6 is depicted just being rotated by 45 degrees. Here, the case of a chromeless PSM is displayed, necessitating equal size surface areas (Fig. 7b), since there is nearly no attenuation. In Fig. 7a a mask is shown, which does not fulfill the conditions according to the present invention. Frequency doubling occurs only in the case of the basic shapes shown in Fig. 7b, which can be seen on the right hand sides of Figs. 7a and b.

Another embodiment of basic shapes in chromeless PSM is shown in Fig. 8. The shape according to the present invention results in elongated imaged structures on the wafer, which can be modeled to handle line shortening. By expanding the structures or portions of a pattern in the y-direction of Fig. 8, the elongation of the resulting imaged structures on the wafer can also be varied in the y-direction - without losing the condition of vanishing zero-order-diffraction and thus frequency doubling. Transferring the embodiment of Fig. 8 to the case of attenuated phase-shift masks, the U-form in combination with the rectangle giving the basic shape according to Fig. 8 is modified to obey the condition of the present invention as can be seen in Fig. 9.





## Claims:

1. Phase-shift mask (1) having at least one first pattern (3), which is arranged in a two-dimensional matrix with a multiple of second patterns, which are substantially identical to said first pattern (3), said first pattern comprising:
- at least a first portion (101) having
    - i) a first area,
    - ii) a first transmission of electrical field strength of light, to be irradiated through said mask (1),
    - iii) a first phase-shift exerted on light traversing said mask (1) through said first portion,
  - at least a second portion (102, 100) having
    - i) a second area,
    - ii) a second transmission of electrical field strength of light to be irradiated through said mask (1),
    - iii) a second phase-shift exerted on light traversing said mask through said second portion, said second phase-shift being different from said first phase-shift,
- characterised in that
- the product of said first area of said first portion (101) times said first transmission,
- is substantially equal to
- the product of said second area of said second portion (102, 100) times said second transmission.
2. Phase-shift mask (1) according to claim 1, characterised by said first and second transmission being different from each other.
3. Phase-shift mask (1) according to claim 1, characterised by said first and second transmission having substantially the same value.

4. Phase-shift-mask (1) according to claims 1 or 3,  
c h a r a c t e r i s e d    b y  
a third portion (11) of said first pattern (3), which is not  
transparent for light.

5

5. Phase-shift-mask (1) according to anyone of claims 1 to 4,  
c h a r a c t e r i s e d    b y

- a first width of said first portion and a second width of  
said second portion, said first and second widths extending  
10    in a first direction, the ratio of said first width to said  
second width being different from 1,
- a first length of said first portion and a second length of  
said second portion, said first and second lengths extend-  
ing in a second direction, which is orthogonal to said  
15    first direction, the ratio of said first length to said  
second width being different from 1.

6. Phase-shift mask (1) according to anyone of claims 1 - 3,  
c h a r a c t e r i s e d    i n    t h a t  
20    each of said portions (101, 102, 100) of said first pattern  
(3) is symmetric about at least one axis.

7. Phase-shift mask (1) according to claim 4,  
c h a r a c t e r i s e d    i n    t h a t  
25    each of said portions (101, 102, 100) of said first pattern  
is symmetric about two orthogonal axes.

8. Phase-shift mask (1) according to anyone of claims 1 - 6,  
c h a r a c t e r i s e d    i n    t h a t  
30    - said first portion (101) comprises a square, and  
- said second portion (102, 100) comprises a set of four  
lines bordering and enclosing four sides of said square of  
said first portion.

35    9. Phase-shift mask (1) according to anyone of claim 1 - 6,  
c h a r a c t e r i s e d    i n    t h a t

- said first portion (101) comprises a first sub-pattern being a U-shaped,
- said second portion (102) comprises a second sub-pattern being U-shaped,
- 5 - open ends of said U-shapes are orientated towards each other,
- said first portion (101) comprises a third rectangular sub-pattern, which is enclosed on three sides by said second sub-pattern of said second portion,
- 10 - said second portion (102) comprises a fourth rectangular sub-pattern, which is enclosed on three sides by said first sub-pattern of said second portion.

10. Phase-shift mask according to claim 1 or 2,  
 15 c h a r a c t e r i s e d i n t h a t  
 said first and second transmission are larger than 45 percent of the irradiated light.

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## Abstract

## Phase-shift mask

5 The relative surface area sizes of portions (101, 102) having  
distinct phase-shift and transmission of light of a pattern  
(3) on a phase-shift mask (1) substantially obey the conditi-  
on, that the product of surface area and transmission of te-  
lectrical field strength (40) is the same for all of the por-  
10 tions. Then, frequency doubling occurs due to vanishing zero  
order diffraction orders and in the case of high-transition  
attenuated phase-shift masks a large first order diffraction  
amplitude reveals an even an improved as compared with con-  
ventional phase-shift masks. Two-dimensional matrix-like  
15 structures particularly on attenuated - or halftone - phase-  
shift masks can be arranged to image high-density patterns  
(3) on a semiconductor wafer (2). The duty cycles of pattern  
(5) matrices can be chosen being different from one in two  
orthogonal directions nevertheless leading to frequency dou-  
20 bling.

Figure 7

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Fig. 1

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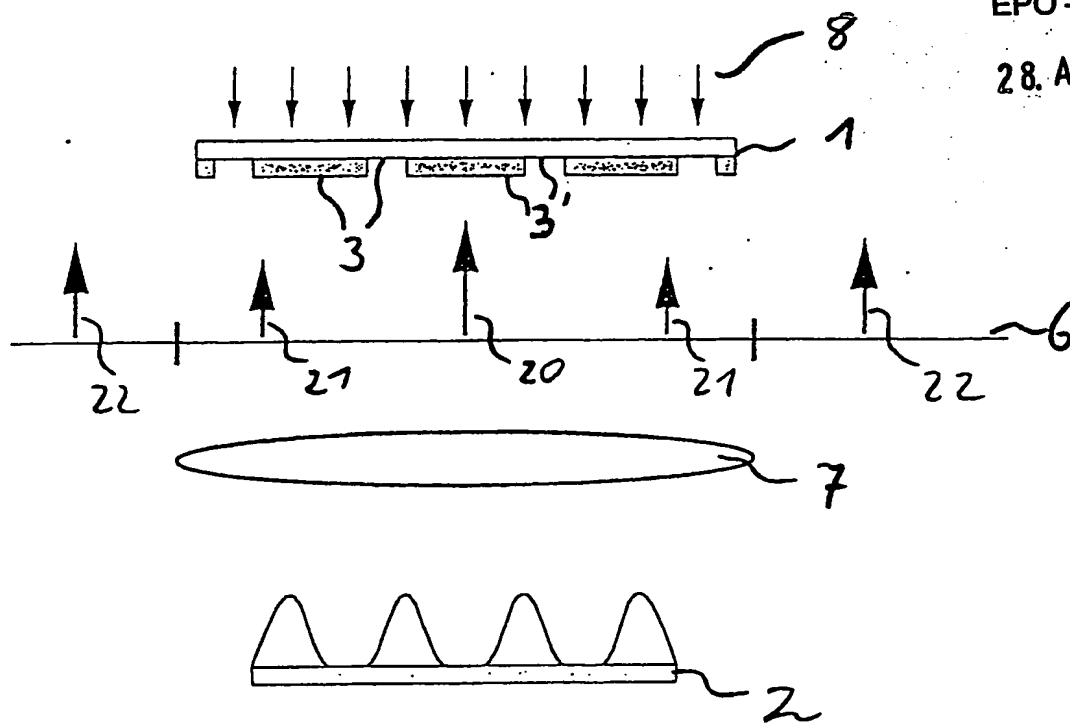


Fig. 2

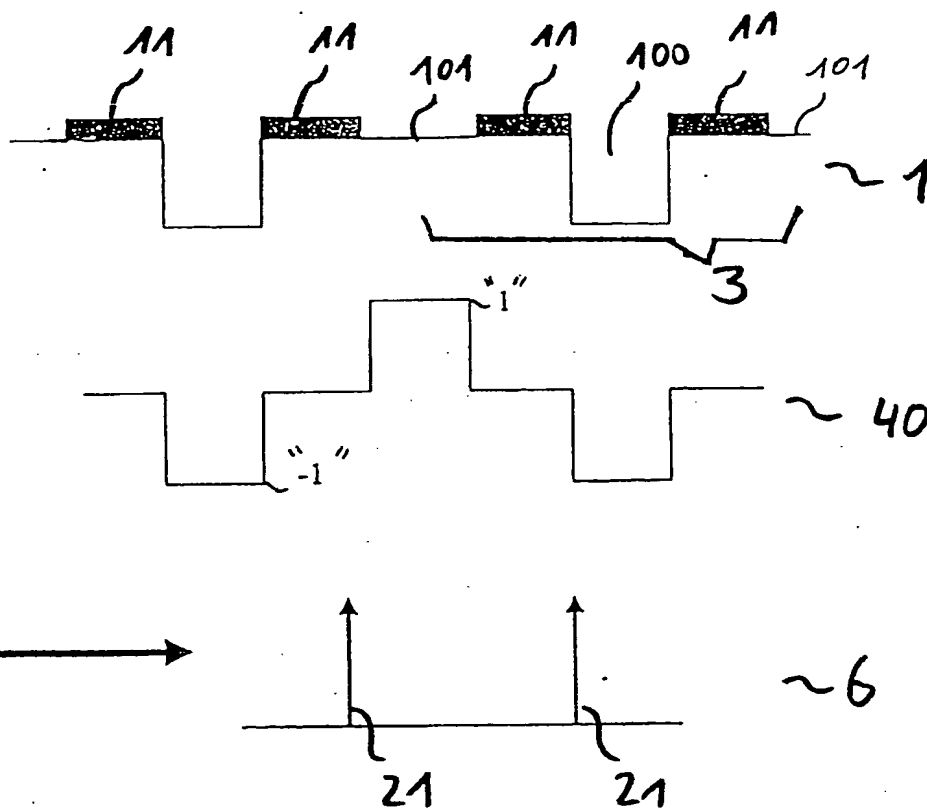


Fig. 3

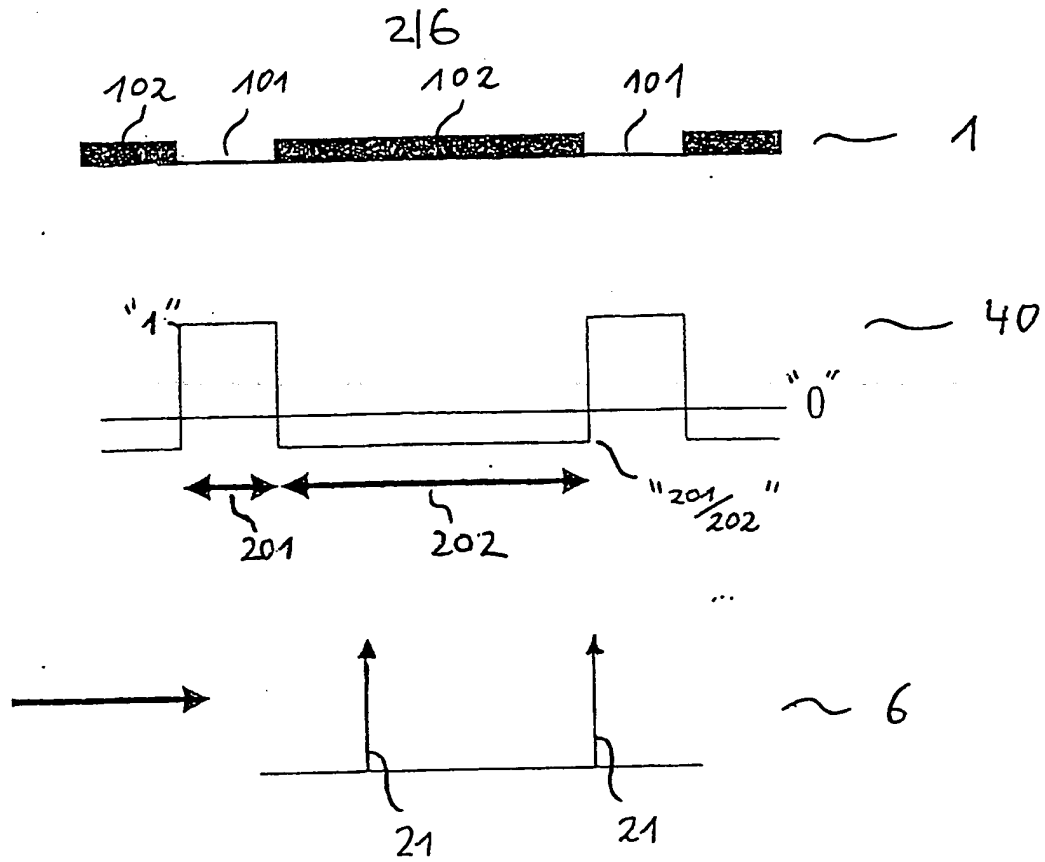


Fig. 4

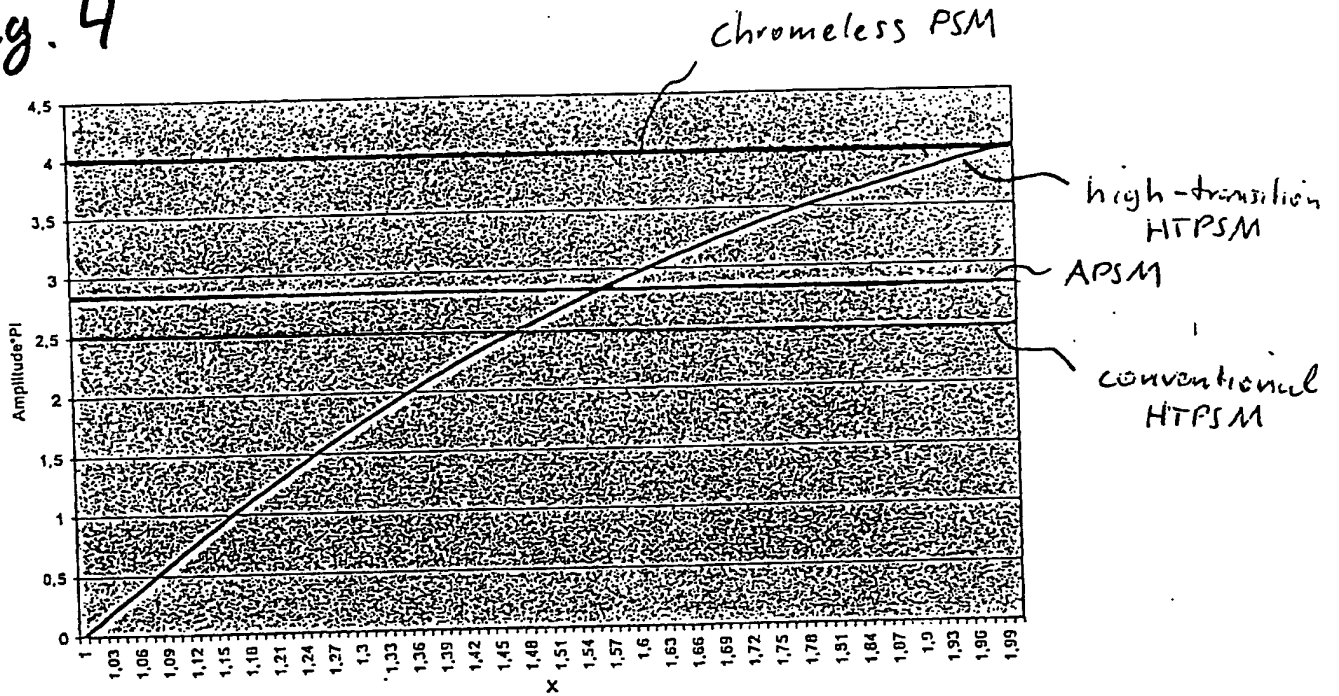
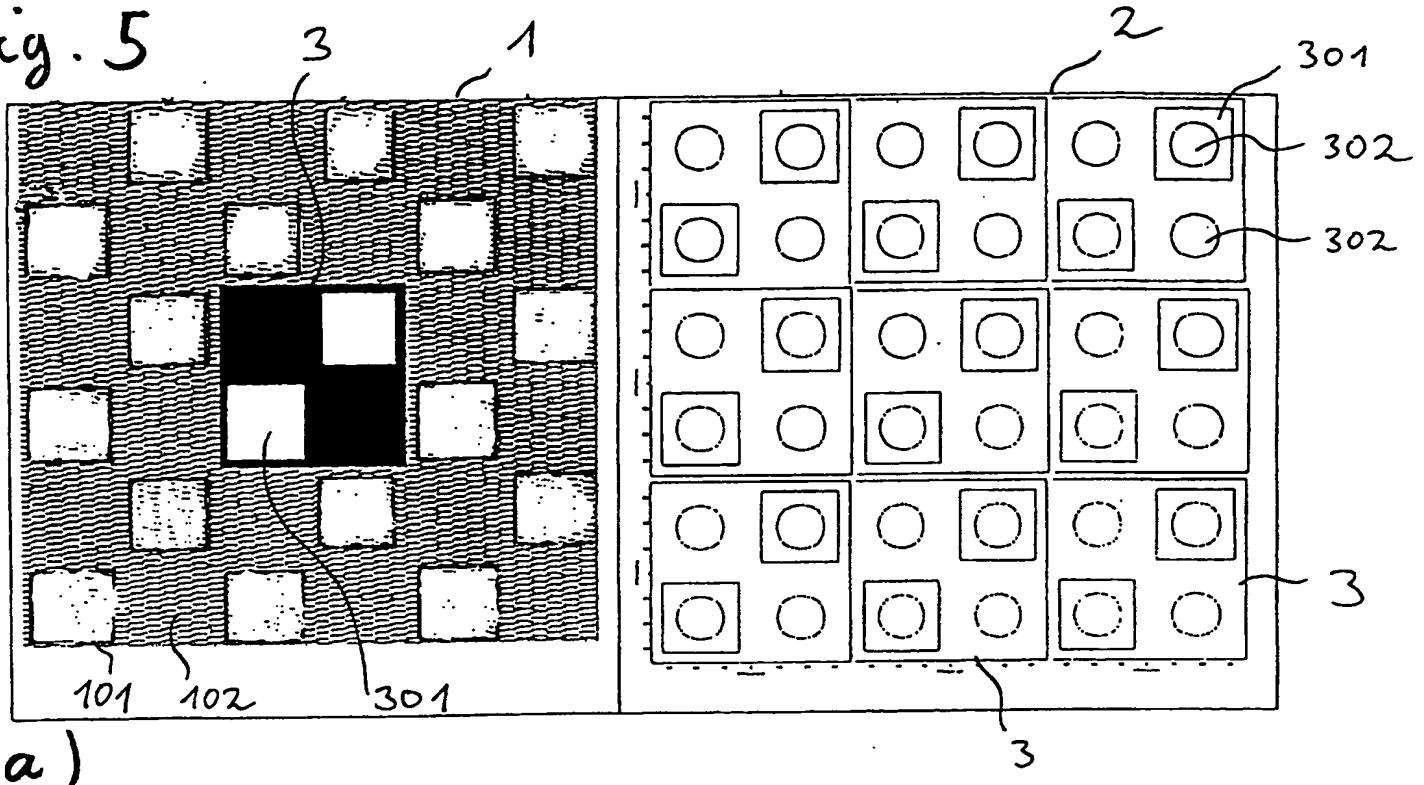
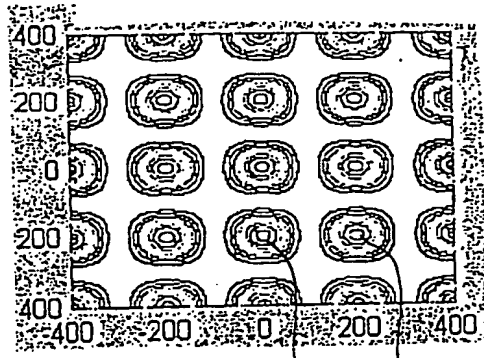
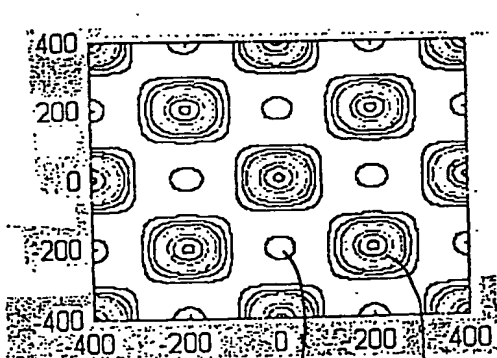




Fig. 5



a)



b)

Fig. 6

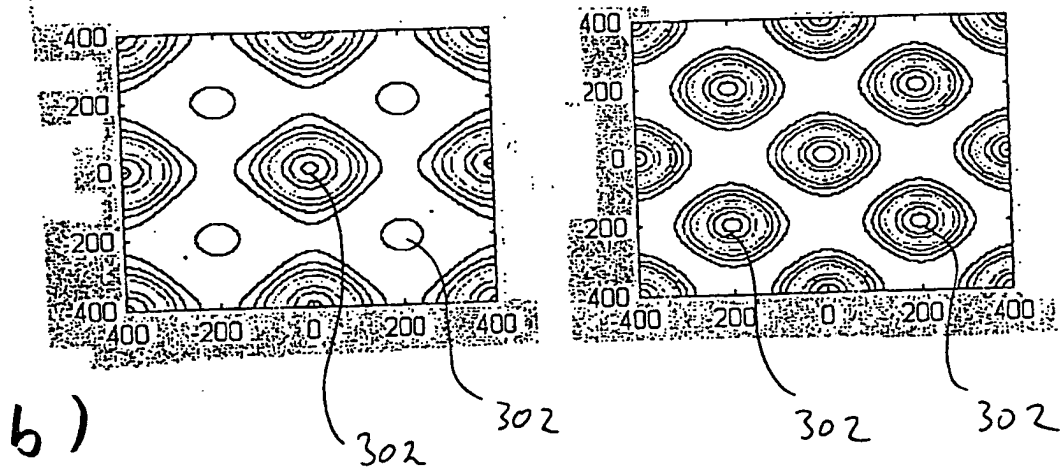
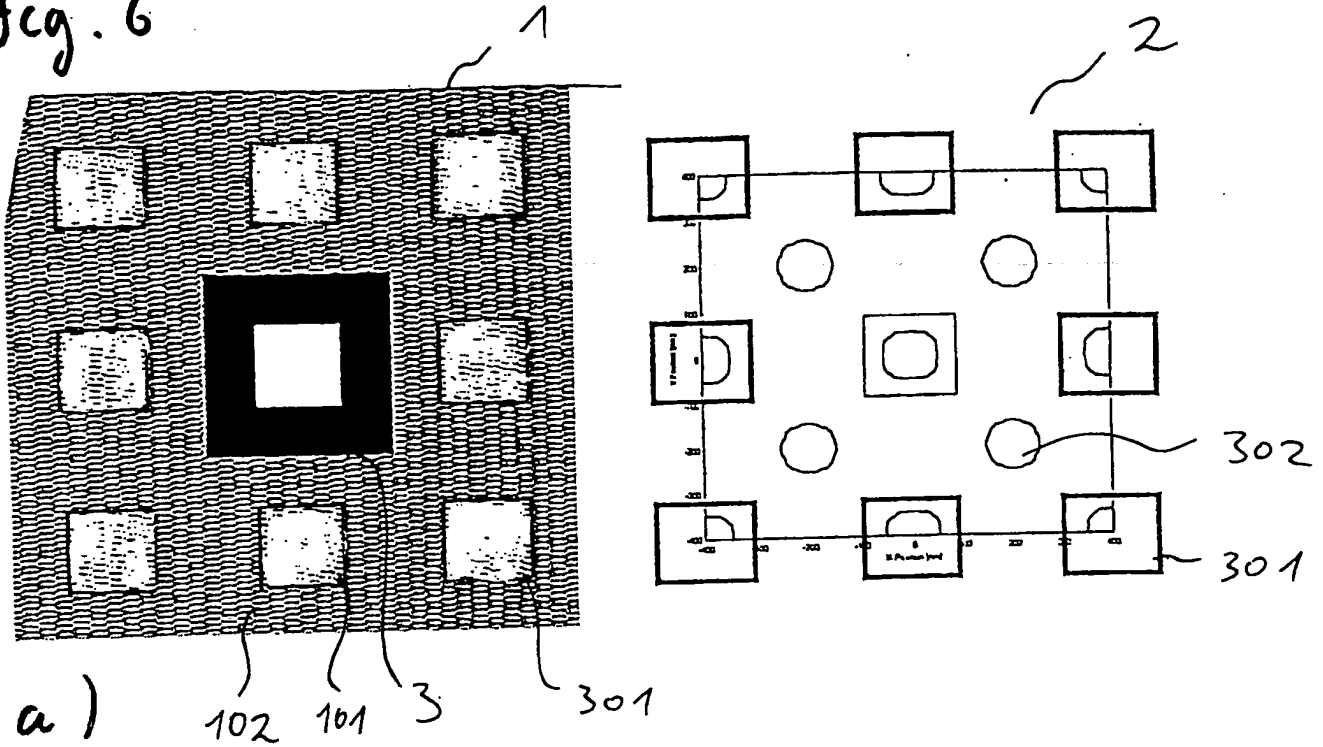


Fig. 7

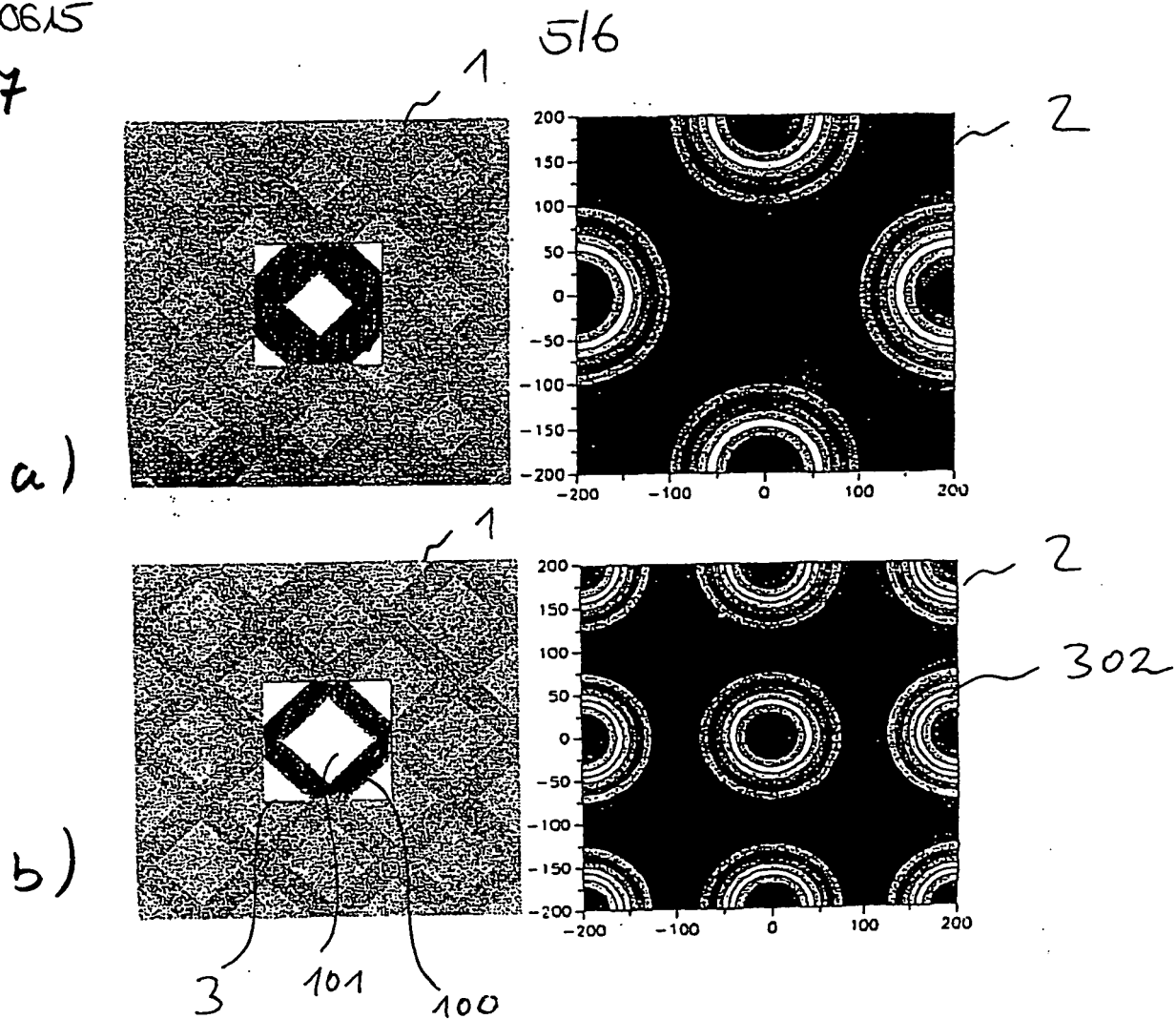


Fig. 8

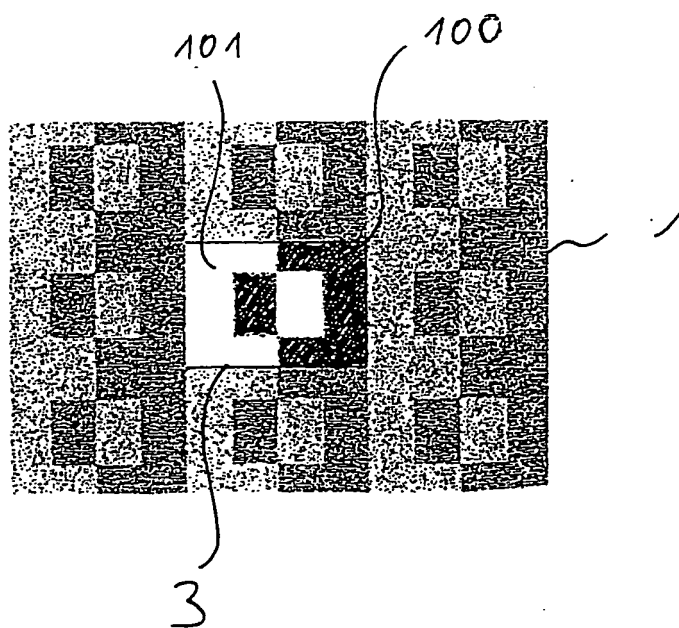


Fig. 9

